

## 描述 / Descriptions

DFN 2×2B-6L 塑封封装 P 沟道 MOS 场效应管。

P-Channel Enhancement Mode Field Effect Transistor in a DFN 2×2B-6L Plastic Package.

## 特征 / Features

$V_{DS} (V) = -16V$      $I_D = -11A$

$R_{DS(ON)}@-4.5V \leq 32m\Omega$

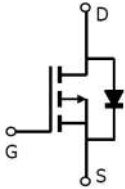
无卤产品。HF Product.

## 用途 / Applications

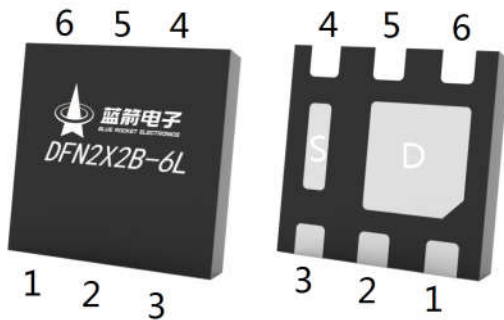
用于电源管理，便携式设备和电池供电系统。

Power Management in Notebook computer, Portable Equipment and Battery powered systems.

## 内部等效电路 / Equivalent Circuit



## 引脚排列 / Pinning



| 出脚   | 定义 |
|------|----|
| Pin1 | D  |
| Pin2 | D  |
| Pin3 | G  |
| Pin4 | S  |
| Pin5 | D  |
| Pin6 | D  |

## 印章代码 / Marking

见印章说明 See Marking Instructions.

**极限参数 / Absolute Maximum Ratings(Tc=25°C)**

| 参数<br>Parameter                        | 符号<br>Symbol                     | 数值<br>Rating | 单位<br>Unit |
|--|----------------------------------|--------------|------------|
| Drain-Source Voltage                   | $V_{DSS}$                        | -16          | V          |
| Gate-Source Voltage                    | $V_{GSS}$                        | $\pm 8$      | V          |
| Continuous Drain Current               | $I_D$                            | -11          | A          |
| Pulsed Drain Current                   | $I_{DM}$                         | -44          | A          |
| Avalanche Current                      | $I_{AS}$                         | 21           | A          |
| Avalanche energy L=0.5mH               | $E_{AS}$                         | 308          | mJ         |
| Power Dissipation for Single Operation | $P_D$                            | 15.5         | W          |
| Maximum Junction Temperature           | $T_j$                            | 150          | °C         |
| Storage Temperature Range              | $T_{stg}$                        | -55 ~ 150    | °C         |
| Thermal Resistance-Junction to Ambient | $R_{\theta JC}$ ( $t \leq 10s$ ) | 8            | °C/W       |

## 电性能参数 / Electrical Characteristics(Tc=25°C)

| 参数<br>Parameter                   | 符号<br>Symbol | 测试条件<br>Test Conditions  | 最小值<br>Min | 典型值<br>Typ | 最大值<br>Max | 单位<br>Unit |
|-----------------------------------|--------------|--|------------|------------|------------|------------|
| Drain-Source Breakdown Voltage    | $BV_{DSS}$   | $I_D=-250\mu A$ $V_{GS}=0V$  | -16        | -18        |            | V          |
| Zero Gate Voltage Drain Current   | $I_{DSS}$    | $V_{DS}=-16V$ $V_{GS}=0V$  |            |            | -1.0       | $\mu A$    |
| Gate-Body leakage current         | $I_{GSS}$    | $V_{DS}=0V$ $V_{GS}=\pm 8V$  |            |            | $\pm 100$  | nA         |
| Gate Threshold Voltage            | $V_{GS(th)}$ | $V_{DS}=V_{GS}$ $I_D=-250\mu A$                                    | -0.5       | -0.6       | -1.0       | V          |
| Static Drain-Source On-Resistance | $R_{DS(ON)}$ | $V_{GS}=-4.5V$ $I_D=-2.0A$   |            | 27         | 32         | m $\Omega$ |
|                                   |              | $V_{GS}=-2.5V$ $I_D=-2.0A$   |            | 37.3       | 42         |            |
|                                   |              | $V_{GS}=-1.8V$ $I_D=-2.0A$   |            | 51         | 60         |            |
| Diode Forward Voltage             | $V_{SD}$     | $I_S=-1A$ $V_{GS}=0V$  |            | 0.75       |            | V          |
| Total Gate Charge                 | $Q_g$        | $V_{GS}=-4.5V$ $V_{DS}=-10V$<br>$I_D=-8A$                          |            | 16         |            | nC         |
| Gate-Source Charge                | $Q_{gs}$     |  |            | 2.5        |            |            |
| Gate-Drain Charge                 | $Q_{gd}$     |  |            | 3.5        |            |            |
| Input Capacitance                 | $C_{iss}$    | $V_{GS}=0V$ $V_{DS}=-25V$<br>$f=1MHz$                              |            | 740        |            | pF         |
| Output Capacitance                | $C_{oss}$    |  |            | 290        |            |            |
| Reverse Transfer Capacitance      | $C_{rss}$    |  |            | 190        |            |            |
| Turn-on Delay Time                | $t_{d(ON)}$  | $V_{GS}=-4.5V$ $V_{DS}=-10V$<br>$R_L=1.25\Omega$ $R_{GEN}=3\Omega$ |            | 7.2        |            | ns         |
| Turn-on Rise Time                 | $t_r$        |  |            | 29         |            |            |
| Turn-off Delay Time               | $t_{d(OFF)}$ |  |            | 100        |            |            |
| Turn-off Fall Time                | $t_f$        |  |            | 50         |            |            |

电参数曲线图 / Electrical Characteristic Curve

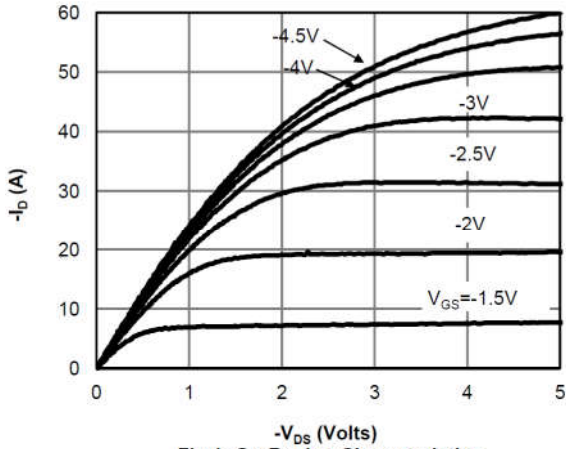


Fig 1: On-Region Characteristics

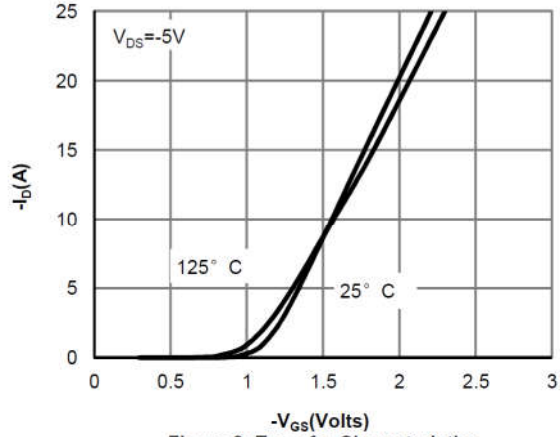


Figure 2: Transfer Characteristics

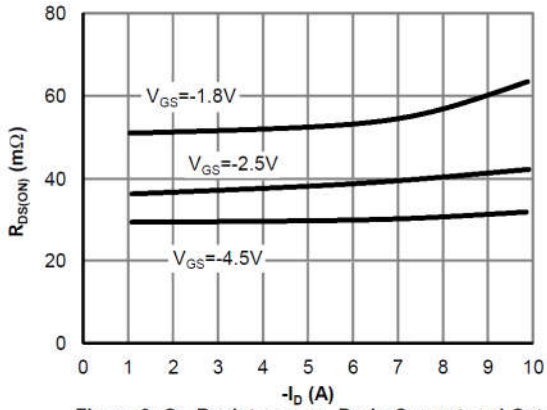


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

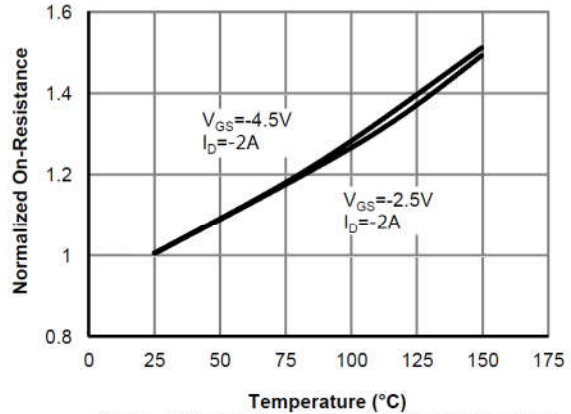


Figure 4: On-Resistance vs. Junction Temperature

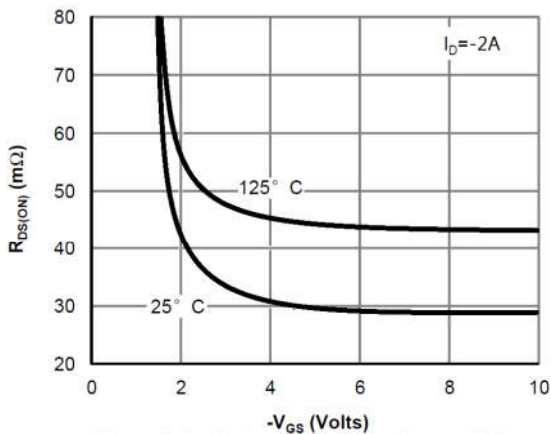


Figure 5: On-Resistance vs. Gate-Source Voltage

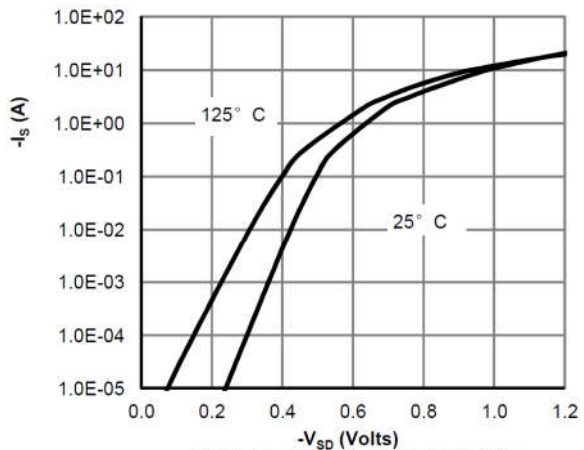


Figure 6: Body-Diode Characteristics

电参数曲线图 / Electrical Characteristic Curve

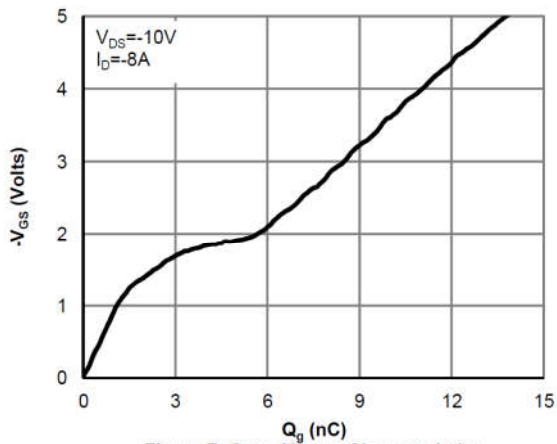


Figure 7: Gate-Charge Characteristics

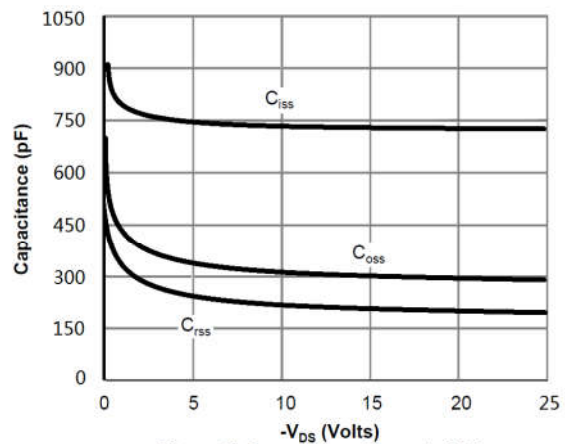


Figure 8: Capacitance Characteristics

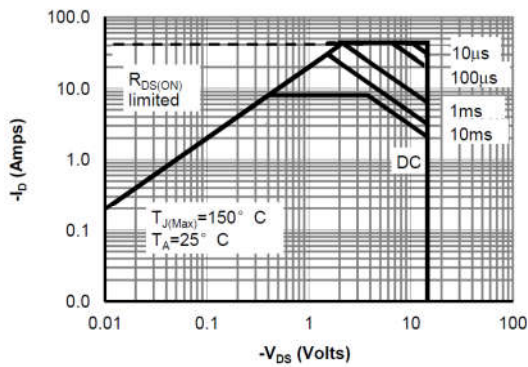


Figure 9: Maximum Forward Biased Safe Operating Area

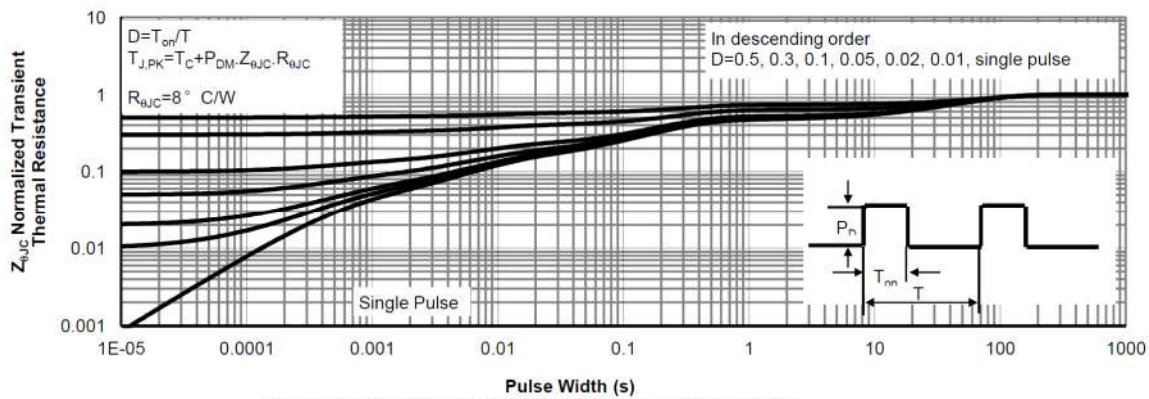


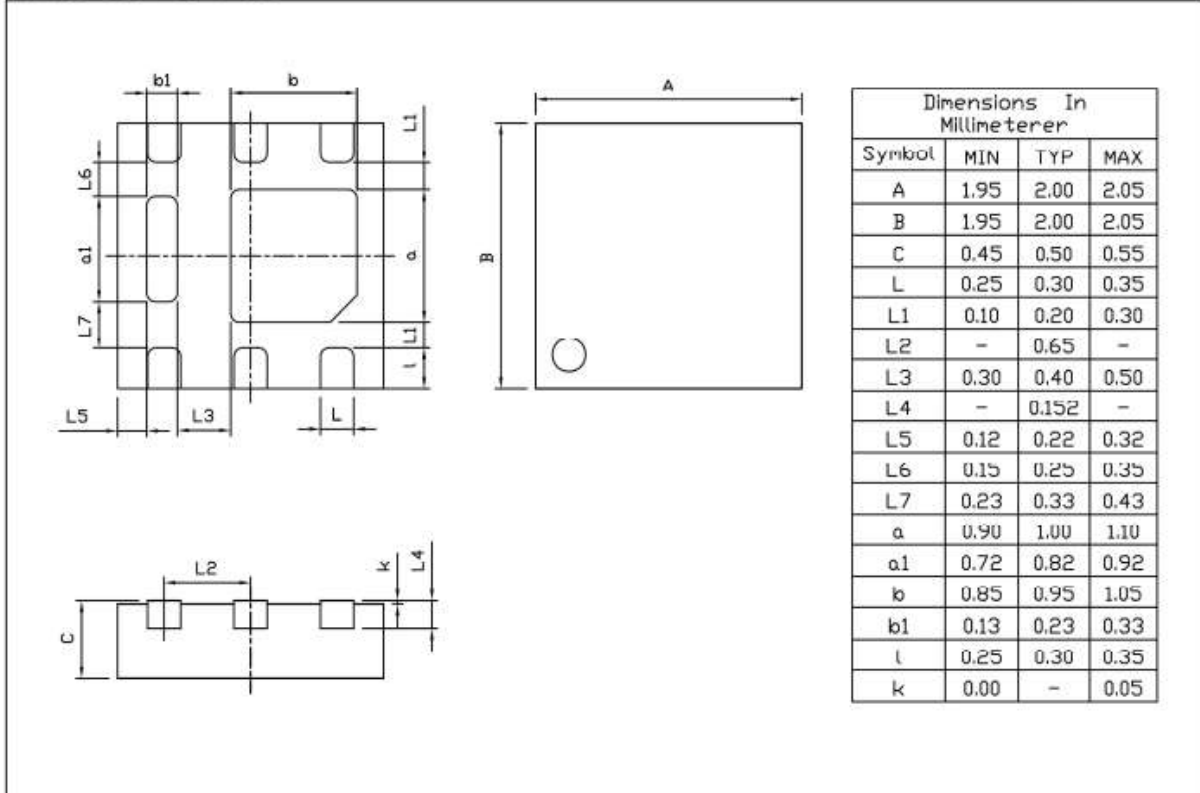
Figure 10: Normalized Maximum Transient Thermal Impedance

外形尺寸图 / Package Dimensions

**DFN2×2B-6L-0.5 外形尺寸图**

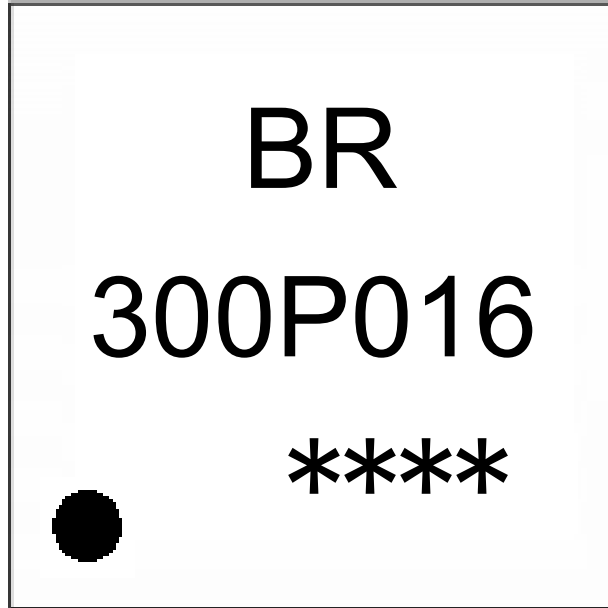
DFN2×2B-6L-0.5

Unit:mm



Rev.01 202006

印章说明 / Marking Instructions



说明：

BR： 为公司代码

300P016： 为型号代码

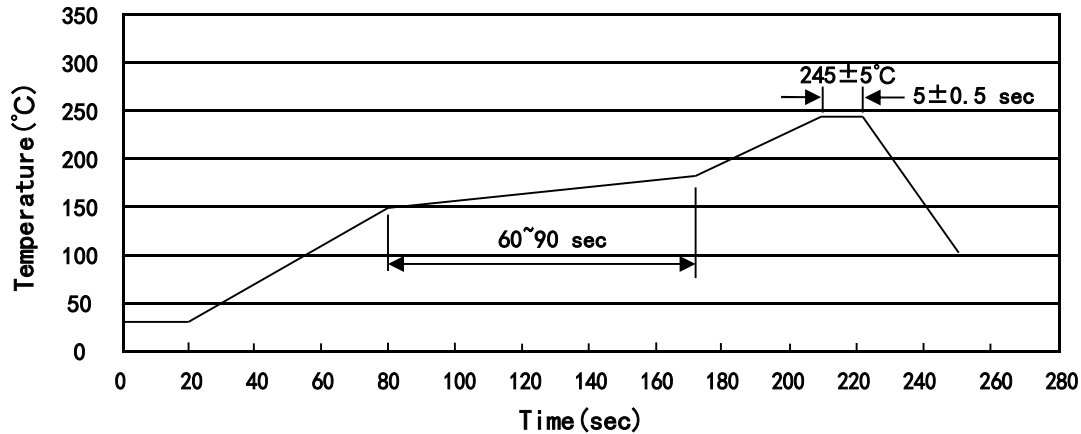
\*\*\*\*： 为生产批号代码，随生产批号变化

Note:

BR: Company Code

300P016: Product Type

\*\*\*\*: Lot No. Code, code change with Lot No

**回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)**


说明：

- 1、预热温度 150~180°C，时间 60~90sec;
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2~10°C/sec.

Note:

- 1.Preheating:150~180°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

**耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions**

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

**包装规格 / Packaging SPEC.**

卷盘包装 / REEL

| Package Type<br>封装形式 | Units 包装数量         |                         |                        |                              |                        | Dimension 包装尺寸 (unit: mm <sup>3</sup> ) |             |             |
|----------------------|--------------------|-------------------------|------------------------|------------------------------|------------------------|---|-------------|-------------|
|                      | Units/Reel<br>只/卷盘 | Reels/Inner Box<br>卷盘/盒 | Units/Inner Box<br>只/盒 | Inner Boxes/Outer Box<br>盒/箱 | Units/Outer Box<br>只/箱 | Reel                                    | Inner Box 盒 | Outer Box 箱 |
| DFN 2×2B-6L          | 4,000              | 10                      | 40,000                 | 4                            | 160,000                | 7" ×8                                   | 210×205×205 | 445×230×435 |

**使用说明 / Notices**